

MMBT4125"供应商

PNP EPITAXIAL SILICON TRANSISTOR

T-29-19

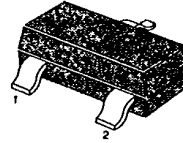
GENERAL PURPOSE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-Base Voltage	V <sub>EB0</sub>	4	V
Collector Current	I <sub>C</sub>	200	mA
Collector Dissipation	P <sub>C</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C

• Refer to MMBT 3906 for graphs

SOT-23



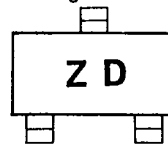
1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	30		V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA, I <sub>E</sub> = 0	30		V
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	4		V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 20V, I <sub>E</sub> = 0		50	nA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> = 0		50	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 2.0mA	50	150	
		V <sub>CE</sub> = 1V, I <sub>C</sub> = 50mA	25		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA		0.4	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA		0.95	V
Current Gain-Bandwidth Product	f <sub>T</sub>	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 20V f = 100MHz	200		MHz
Collector Base Capacitance	C <sub>cb</sub>	V <sub>CB</sub> = 5V, I <sub>E</sub> = 0 f = 100KHz		4.5	pF
Noise Figure	NF	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 5V R <sub>S</sub> = 1KΩ, f = 10Hz to 15.7KHz		5	dB

\* Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Marking



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